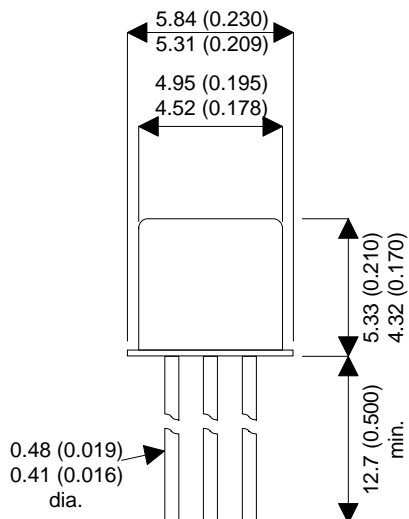
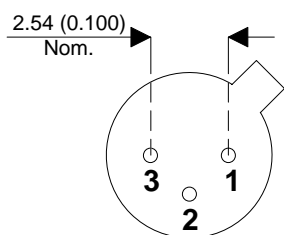


MECHANICAL DATA

Dimensions in mm (inches)



**HIGH VOLTAGE
PNP SILICON
TRANSISTOR**



TO-18 PACKAGE

PIN 1 – Emitter PIN 2 – Base PIN 3 – Collector

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage		200V
V_{CEO}	Collector – Emitter Voltage		200V
V_{EBO}	Emitter – Base Voltage		5V
I_C	Continuous Collector Current		0.5A
P_D	Total Device Dissipation	$T_{AMB} = 25^\circ\text{C}$	0.5W
		Derate above 25°C	2.86mW/ $^\circ\text{C}$
P_D	Total Device Dissipation	$T_C = 25^\circ\text{C}$	2.5W
		Derate above 25°C	14.3mW/ $^\circ\text{C}$
T_J, T_{STG}	Operating Junction & Storage Temperature Range		-65 to 200°C
$R_{\theta JC}$	Thermal Resistance, Junction – Case		70 $^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
OFF CHARACTERISTICS						
$V_{(BR)CEO}$	Collector – Emitter Breakdown Voltage	$I_C = 10\text{mA}$ $I_B = 0$	200		V	
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	$I_C = 100\mu\text{A}$ $I_E = 0$	200			
$V_{(BR)EBO}$	Emitter – Base Breakdown Voltage	$I_E = 100\mu\text{A}$ $I_C = 0$	6			
I_{CBO}	Collector Cut-off Current	$V_{CB} = 150\text{V}$ $I_E = 0$		50	nA	
I_{CEO}	Collector Cut-off Current	$V_{CE} = 150\text{V}$ $I_B = 0$		500		
I_{EBO}	Emitter Cut-off Current	$V_{BE} = 5\text{V}$ $I_C = 0$		50		
ON CHARACTERISTICS						
h_{FE}	DC Current Gain	$V_{CE} = 1\text{V}$ $I_C = 0.1\text{mA}$	20		—	
		$V_{CE} = 10\text{V}$ $I_C = 1\text{mA}$	30			
		$V_{CE} = 10\text{V}$ $I_C = 10\text{mA}$	35			
		$V_{CE} = 10\text{V}$ $I_C = 30\text{mA}$	35	150		
$V_{CE(sat)}$	Collector – Emitter Saturation Voltage	$I_C = 10\text{mA}$ $I_B = 1\text{mA}$		0.3	V	
		$I_C = 30\text{mA}$ $I_B = 3\text{mA}$		1.3		
$V_{BE(sat)}$	Base – Emitter Saturation Voltage	$I_C = 10\text{mA}$ $I_B = 1\text{mA}$		0.8	V	
		$I_C = 30\text{mA}$ $I_B = 3\text{mA}$		0.9		
DYNAMIC CHARACTERISTICS						
f_t	Current Gain Bandwidth Product	$I_C = 20\text{mA}$ $V_{CE} = 20\text{V}$ $f = 20\text{MHz}$	50	110	200	MHz
C_{ob}	Output Capacitance	$I_E = 0$ $V_{CB} = 20\text{V}$ $f = 1\text{MHz}$		3.5		pF
C_{ib}	Input Capacitance	$I_C = 0$ $V_{EB} = 0.5\text{V}$ $f = 1\text{MHz}$		45		
t_{on}	Turn-On Time	$I_{B1} = 10\text{mA}$ $I_C = 50\text{mA}$ $V_{CC} = 100\text{V}$		100		ns
t_{off}	Turn-Off Time	$I_{B2} = 10\text{mA}$ $I_C = 50\text{mA}$ $V_{CC} = 100\text{V}$		400		

* Pulse Test: $t_p = 300\mu\text{s}$, $\delta \leq 1\%$.



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